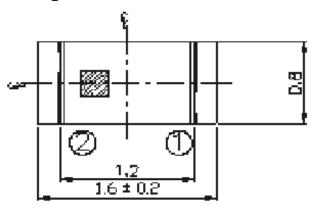
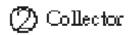
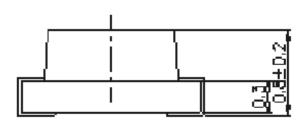
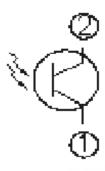
## **Package Dimensions**



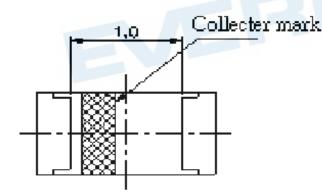
Emitter

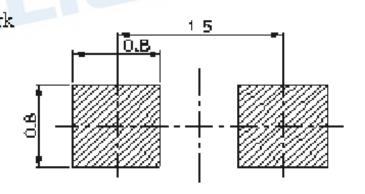






For reflaw soldering (Propose)





Notes:

- 1.All dimensions are in millimeters
  - 2.Tolerances unless dimensions ±0.1mm
- 3. Suggested pad dimension is just for reference only Please modify the pad dimension based on individual need

# Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Collector-Voltage	V <sub>ECO</sub>	5	V
Collector Current	I <sub>C</sub>	20	mA
Operating Temperature	$T_{opr}$	-25 ~ +85	$^{\circ}\!\mathbb{C}$
Storage Temperature	T <sub>stg</sub>	-40 ~ +85	$^{\circ}\!\mathbb{C}$
Soldering Temperature *1	T <sub>sol</sub>	260	°C
Power Dissipation at(or below) 25°C Free Air Temperature	P <sub>d</sub>	75	mW

**Notes:** \*1: Soldering time ≤ 5 seconds.

# **Electro-Optical Characteristics (Ta=25°C)**

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Rang Of Spectral Bandwidth	λ <sub>0.5</sub>		730		1100	nm
Wavelength Of Peak Sensitivity	$\lambda_{P}$			940		nm
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =100µA Ee=0mW/cm <sup>2</sup>	30			V
Emitter-Collector Breakdown Voltage	BV <sub>ECO</sub>	I <sub>E</sub> =100μA Ee=0mW/cm²	5			V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =2mA Ee=1mW/cm <sup>2</sup>			0.4	V
Collector Dark Current	I <sub>CEO</sub>	V <sub>CE</sub> =20V Ee=0mW/cm <sup>2</sup>			100	nA
On State Collector Current	I <sub>C(ON)</sub>	V <sub>CE</sub> =5V Ee=1mW/cm <sup>2</sup>	0.3	0.6		mA

## **Intensity Specifications for Bin Grading:**

	-			
Rank	Test condition	Min	Max	Unit
BIN 2	VCE=5V Ee=1mW/cm <sup>2</sup> λ P=940nm	0.30	0.82	
BIN 3		0.70	1.90	
BIN 4		1.14	2.60	
BIN5		1.77	3.61	mA
BIN6		2.67	5.07	
BIN7		3.54	7.07	
BIN8		>5	.00	



## **Typical Electro-Optical Characteristics Curves**

Ta=25°C

0.8

0.6

0.4

900

1000

Wavelength  $\lambda$  (nm)

1100

1300

Fig.2 Collector Current vs
rradiance

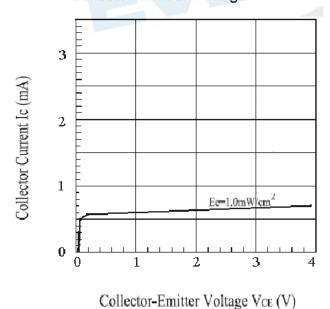
10
Vcr=5V
Ta=25 °C

0.01
0.01
0.01
0.01
1
1
10
Irradiance Ee (mW/cm²)

Fig.3 Collector Current vs

Collector-Emitter Voltage

800



Relative Spectral Sensitivity

0.2

0

700

#### **Precautions For Use**

#### 1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (Burn out will happen).

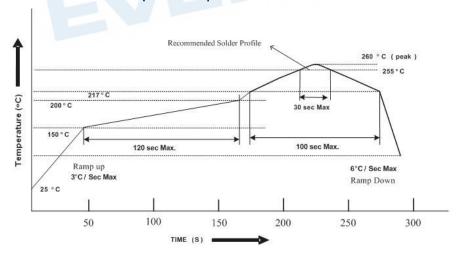
#### 2. Storage

- 2.1 Do not open moisture proof bag before the products are ready to use.
- 2.2 Before opening the package, the Phototransistor should be kept at 10°C~30°C and 90%RH or less.
- 2.3 The Phototransistor suggested be used within one year.
- 2.4 After opening the package, the devices must be stored at 10°C ~30°C and ≤ 60%RH, and used within 168 hours (floor life). If unused Phototransistor remain, it should be stored in moisture proof packages.
- 2.5 If the moisture absorbent material (desiccant material) has faded or unopened bag has exceeded the shelf life or devices (out of bag) have exceeded the floor life, baking treatment is required.
- 2.6 If baking is required, refer to IPC/JEDEC J-STD-033 for bake procedure or recommend the following conditions:

96 hours at 60°C ± 5°C and <5 % RH (reeled/tubed/loose units)

#### 3. Soldering Condition

3.1 Lead solder temperature profile



- 3.2 Reflow soldering should not be done more than two times.
- 3.3 When soldering, do not put stress on the Phototransistor during heating.
- 3.4 After soldering, do not warp the circuit board.

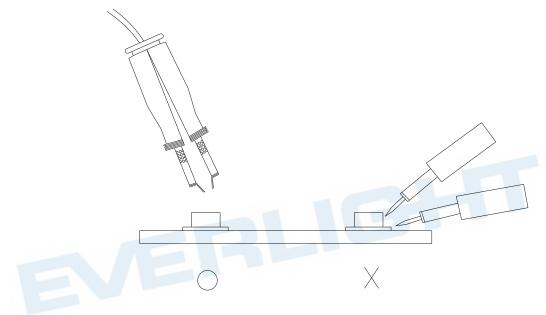
6

#### 4. Soldering Iron

Each terminal is to go to the tip of soldering iron temperature less than 350°C for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

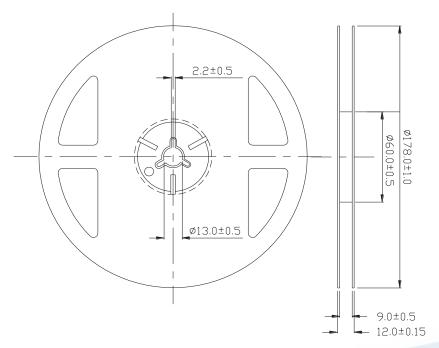
### 5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.



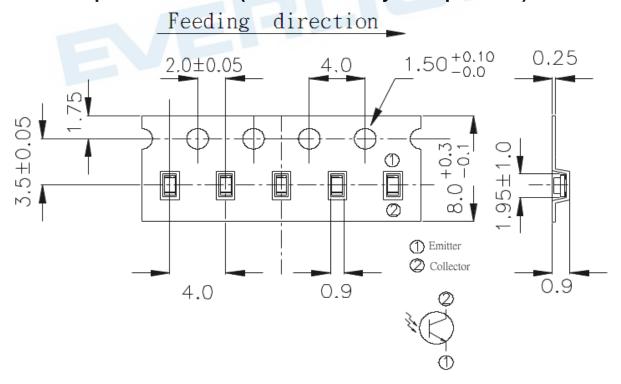
狀態:Approved(正式發行)

### **Package Dimensions**



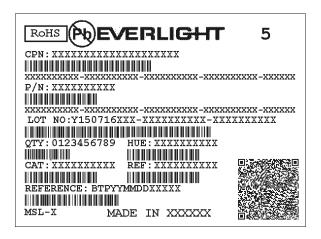
**Note:** The tolerances unless mentioned are ±0.1mm, Unit: mm

# Carrier Tape Dimensions: (Loaded Quantity: 3000pcs/Reel)



**Note:** The tolerances unless mentioned are ±0.1, unit=mm

### **Label Form Specification**



P/N: Production Number

LOT No: Lot Number QTY: Packing Quantity **HUE: Peak Wavelength** 

CAT: Ranks REF: Reference MSL-X: MSL Level

Made In: MSanufacture place

#### **DISCLAIMER**

- 1. EVERLIGHT reserves the right(s) on the adjustment of product material mix for the specification.
- 2. The product meets EVERLIGHT published specification for a period of twelve (12) months from date of shipment.
- 3. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
- 4. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from the use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
- 5. These specification sheets include materials protected under copyright of EVERLIGHT. Reproduction in any form is prohibited without obtaining EVERLIGHT's prior consent.
- 6. This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or life saving applications or any other application which can result in human injury or death. Please contact authorized Everlight sales agent for special application request.

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